

MPS6518



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA. Sourced from Process 66. See 2N3906 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPS6518	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
Reuc	Thermal Resistance, Junction to Case	83.3	°C/W
R _{eJA}	Thermal Resistance, Junction to Ambient	200	°C/W

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 0.5 \text{ mA}, I_B = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.0		V
сво	Collector Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, T _A = 60°C	0.5 1.0		μ Α μ Α
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_{C} = 2.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 100 \text{ mA}$	150 90	300	
/ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.5	V
SMALL S	IGNAL CHARACTERISTICS				

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%